

Title (en)

SEMICONDUCTOR COMPONENT, SUBSTRATE AND METHOD FOR PRODUCING A SEMICONDUCTOR LAYER SEQUENCE

Title (de)

HALBLEITERBAUELEMENT, SUBSTRAT UND VERFAHREN ZUR HERSTELLUNG EINER HALBLEITERSCHICHTENFOLGE

Title (fr)

COMPOSANT SEMI-CONDUCTEUR, SUBSTRAT ET PROCÉDÉ DE FABRICATION D'UNE SUCCESSION DE COUCHES SEMI-CONDUCTRICES

Publication

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Application

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Abstract (en)

[origin: WO2012007350A1] The invention relates to a semiconductor component (1), comprising a semiconductor body (2), which is based on a nitride compound semiconductor material, and a substrate (3), on which the semiconductor body is disposed. Impurities are deliberately formed in the substrate. The invention further relates to a substrate and to a method for producing a semiconductor layer sequence (20) for a semiconductor component (1).

IPC 8 full level

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